NSN 5962-01-376-1638

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Maximum	Power	Dissin	ation	Rating:
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1.2 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Acmi pods (an/asq-t27) e/i fscm 12339

Features Provided:

Bipolar and electrostatic sensitive and erasable and programmed

Inclosure Configuration:

Leaded chip carrier

Output Logic Form:

Bipolar metal-oxide semiconductor

Input Circuit Pattern:

16 input

Case Outline Source And Designator:

C-2 mil-m-38510

Current Rating Per Characteristic:

-2.00 milliamperes peak forward surge current universal and 12.00 milliamperes peak forward surge current megawatts

Product Name:

Microcircuit, pal cpu clock timing

Voltage Rating And Type Per Characteristic:

-0.5 volts total supply and 7.0 volts total supply

Memory Device Type:

Pal

Hybrid Technology Type:

Monolithic

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). And 96906-mil-std-1686 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 printed circuit

Specification Data:

67268-5962-85155112a government standard and 12339-89014078 manufacturers source control

Departure From Cited Designator:

Altered by programming and marking

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

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